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The longitudinal resistance of a quantum Hall system with a density gradient

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Following recent experiments, we consider current flow in two dimensional electronic systems in the quantum Hall regime where a gradient in the electron density induces a spatial variation in the Hall resistivity. Describing the system in terms of a spatially varying local resistivity tensor, we show that in such a system the current density is generically non-uniform, with the current being pushed towards one side of the sample. We show that, for sufficiently large density gradient, the voltage along that side is determined by the change of the Hall resistivity, and is independent of the microscopic longitudinal resistivity, while the voltage on the opposite side is small and determined by both longitudinal and Hall resistivities. We solve some particular models in detail, and propose ways by which the microscopic longitudinal resistivity may be extracted from measurements of the longitudinal voltage on both sides of the sample.

I. INTRODUCTION

Recent striking experimental observations of transport in high mobility two-dimensional electron gases in the quantum Hall regime have been successfully explained as resulting from density gradients of as small as 1%/cm.[1] These gradients presumably arise from inhomogeneities in the MBE growth.[1] Specifically, the longitudinal voltage drop differs on the two sides of the sample: on one side the voltage drop is close to zero; on the other the voltage drop yields a longitudinal resistance equal to the difference in the *Hall* resistivities corresponding to the densities at the two probes. Thus, the longitudinal resistance of such samples does not measure an intrinsic longitudinal resistivity, ρ_{xx}, but rather probes the (spatially varying) Hall resistivity ρ_{xy}.

The explanation of these observations given in Ref. 1 was based on the edge-state formalism for transport in quantum Hall systems. This formalism is capable of describing inhomogeneous systems consisting of regions of quantized Hall conductance that are separated by sharp boundaries. However, there are many questions that it cannot address, such as how "sharp" must the boundary between the quantized Hall regions be for the edge-state formalism to apply? And how would the transport properties of a *compressible* system, such as the $\nu = 1/2$ composite Fermi liquid,[2] be affected by a density gradient? In this case the sample is at no point in a quantum Hall state so cannot be described within the edge-state formalism.

In this work we employ a more general theoretical approach: we model the experimental system as an inhomogeneous classical conductor,[3,4] with a spatially varying local resistivity tensor set by the inhomogeneous electron density, *with a net density gradient.* Using this model we are able to answer the questions posed above and analyze the relation between the observed transport phenomena and the properties of the quantized Hall effect. As we show below, *under quite general circumstances, the presence of a density gradient results in a non-uniform current density that leads to a difference in the longitudinal voltage drop on the two sides of a Hall bar sample.* We describe the conditions under which the boundary between the quantum Hall states is "sharp" and the edge-state formalism used in Ref. 1 applies; we also determine corrections to this behavior. We discuss in detail the effects of a density gradient on a compressible state. In this case we show that, even in the presence of an *unknown* density gradient, the intrinsic local resistivity ρ_{xx} can in principle be extracted from resistance measurements in a Hall bar geometry.

There have been many previous studies of quantum Hall systems using this approach.[3,4,5,6,7,8] These have shown that, for macroscopically homogeneous samples (when the correlation length of the density inhomogeneities is small compared to the sample size), the measured longitudinal resistance can, depending on the experimental circumstances, be determined by the fluctuations in ρ_{xy} independent of the intrinsic ρ_{xx}:[4,5,6] notably, the height of the peak in the longitudinal resistivity between two quantised Hall states can be equal to the difference in the Hall resistivities of those states.[6] However, in all macroscopically homogeneous systems, the *same* longitudinal voltage drop would appear on the two sides of a Hall bar sample. While a density gradient was invoked in Ref. 8 to account for transport measurements of certain Corbino disk samples,[9] the effects of a density gradient have not been adequately explored. Other works considered related effects due to inhomogeneities in the magnetic field and variations in the sample thickness.[10,11] The paper is organized as follows. After formulating the mathematical problem in §II, in §III we provide general arguments for the transport properties of a system in which voltage probes lie in two different quantized Hall states. We show how the results of Ref. 1 emerge within our theoretical approach. Our conclusions here rely on an assumption that current remains close to one side of the sample. Justification for this assumption is provided by §IV,§V and §VI which contain explicit solutions for particular geometries: in §IV and §V we study a compressible system with a uniform density gradient; in §VI we calculate the effects of a uniform dissipative region between the two quantized Hall regions. Finally, in §VII we provide discussion and conclusions.

II. FORMULATION OF THE PROBLEM

We consider transport in a two-dimensional sample in the $x-y$ plane. The local current density $\mathbf{j}(\mathbf{r})$ is related to the local electric field $\mathbf{E}(\mathbf{r})^{13}$ via

$$\mathbf{E} \;=\; \rho_{xx}\mathbf{j} - \rho_{xy}\hat{\mathbf{z}}\times\mathbf{j} \tag{1}$$

where the components of the resistivity tensor, ρ_{ij}, are also assumed to be functions of position. These variations arise from inhomogeneities in the underlying carrier density in the quantum Hall samples.

In a steady state, the current density and the electric field must satisfy

$$\nabla\cdot\mathbf{j} = 0 \tag{2}$$

$$\nabla\times\mathbf{E} = 0 \tag{3}$$

as well as the appropriate boundary conditions.

We can ensure (3) by defining a scalar potential ϕ, such that

$$\mathbf{E} = -\nabla\phi. \tag{4}$$

Similarly, we can ensure (2), by defining a stream function ψ via

$$\mathbf{j} = \hat{\mathbf{z}}\times\nabla\psi. \tag{5}$$

Then, substituting (1) into (3), the equation for ψ is

$$\rho_{xx}\nabla^2\psi + \nabla\rho_{xx}\cdot\nabla\psi - \hat{\mathbf{z}}\cdot\nabla\psi\times\nabla\rho_{xy} = 0. \tag{6}$$

We shall solve equation (6) using various boundary conditions, and functional dependences of the local resistivity tensor on position.

III. GENERAL ARGUMENTS

We begin our discussion by considering the situation in which the change in density along the sample is sufficient that the two ends of the sample are in different quantized Hall states, A and B. We assume that these regions exhibit good quantized Hall effects, *i.e.* that dissipation is negligible $|\rho_{xx}/\rho_{xy}| \ll 1$. These regions are therefore characterized just by their Hall resistivities ρ_{xy}^A and ρ_{xy}^B. As illustrated in Fig. 1, we imagine that the four voltage probes attached to the sample lie in these regions of quantized Hall resistivity. For now, the details of the resistivity in the intervening region (shown shaded in Fig. 1) are unimportant. Moreover, the precise geometry is not important: the density gradient could be in any direction, or indeed could be nonuniform – we require only that contacts 1 and 4 are in region A, and 2 and 3 in B.

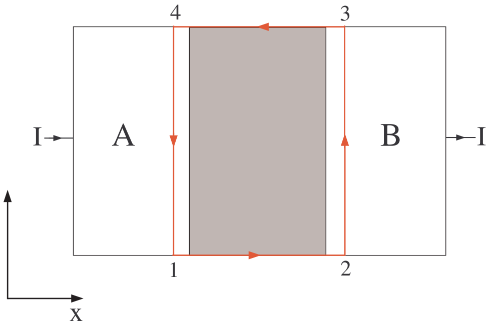

FIG. 1: Geometry of the sample considered. A total current I flows from left to right along the length of the sample. The four voltage probes lie on the sides of the sample within the two quantised Hall regions (A and B) at the two ends. The transport properties of the intervening shaded region are unimportant for the discussion of § III. The contour of integration used for calculating the dissipation integral in the Appendix is shown.

A key result of our work is to show that when a current I is passed along a sample of this type:

(i) the longitudinal voltage drop is larger on one side of the sample than the other, the side being selected by the sign of $\Delta\rho_{xy} \equiv \rho_{xy}^A - \rho_{xy}^B$;

(ii) under physically realistic conditions for the intervening region, the smaller of these two voltages can be exponentially small (in a manner to be discussed in detail below);

(iii) in cases where (ii) applies, the nonzero voltage yields, to exponential accuracy, a longitudinal resistance

$$R = |\Delta\rho_{xy}| \tag{7}$$

That is, the apparent longitudinal resistance is determined by the difference in the *Hall* resistivities at the locations of the two contacts.

These effects are identical to those observed experimentally in Ref. 1, and derived there within the edge state transport formalism. However, we emphasize that our results hold in a much more general setting. For example, we shall show that the two quantized Hall fluids may be joined by a finite region of a compressible quantum Hall fluid where the resistivity tensor is not quantized. Furthermore, we shall be able to account for departures from the limiting behavior of results (ii) and (iii).

First, we prove result (i) by adapting an approach of Ref. 7 to the present geometry. As described in the Appendix, by making use of the fact that the regions A and B have negligible dissipation one finds that, *independent of the spatial distribution of the resistivity between these two regions*, the net power dissipated within the sample is

$$Q = \frac{1}{2}\left(\rho_{xy}^A - \rho_{xy}^B\right)^{-1}\left(V_{43}^2 - V_{12}^2\right) \qquad (8)$$

where

$$V_{12} \equiv \int_{x_1}^{x_2} \mathbf{E}\cdot d\mathbf{l} = \phi(x_1) - \phi(x_2) \qquad (9)$$

$$V_{43} \equiv \int_{x_4}^{x_3} \mathbf{E}\cdot d\mathbf{l} = \phi(x_4) - \phi(x_3) \qquad (10)$$

are the longitudinal voltage drops on the two sides of the sample. Since the dissipated power must be positive, $Q > 0$, Eq.(8) shows that $|V_{43}| > |V_{12}|$ if $\rho_{xy}^A > \rho_{xy}^B$ (and vice versa). This proves result (i); it also identifies which of the voltage drops is the larger for a given sign of $\Delta\rho_{xy}$.

The demonstration of result (ii) will be discussed in the following sections. For now, we note that result (iii) is a direct consequence of (ii) in the geometry described. Let us assume that the necessary conditions have been met that (ii) holds. For simplicity, we imagine that the sample has been oriented such that $\rho_{xy}^A > \rho_{xy}^B$ in which case $|V_{43}| > |V_{12}|$. Then it is V_{12} that is exponentially small and which we now set to zero. We can now evaluate the potential drop V_{43} by integrating the electric field from 4 to 1 to 2 to 3. Using the facts that the paths $4 \rightarrow 1$ and $2 \rightarrow 3$ are in quantized Hall states, and that $V_{12} = 0$, one finds

$$V_{43} = I\left(\rho_{xy}^A - \rho_{xy}^B\right) \qquad (11)$$

$$R_{43} \equiv \frac{V_{43}}{I} = \rho_{xy}^A - \rho_{xy}^B = \Delta\rho_{xy} \qquad (12)$$

This is result (iii), which we now see as a consequence of (ii).

In this section we have asserted that the smaller voltage drop can be exponentially small, as in result (ii). In the following sections we describe the current distributions in particular (physically relevant) situations where exact results can be obtained, and which do show that the smaller voltage drop is, indeed, exponentially small.

IV. TRANSPORT IN A HALL BAR WITH A UNIFORM GRADIENT IN THE HALL RESISTIVITY

We first consider the situation of a long Hall bar aligned with the x-axis, and with edges at $y = 0, w$. We shall discuss the current distribution in a region that is far from the current contacts. We consider the situation in which ρ_{xx} is independent of position, and ρ_{xy} has a constant gradient, $\nabla\rho_{xy}$ (which can be in an arbitrary direction). As is discussed in more detail in §VII, this model can be valid in a sample at a density close to a compressible state and with a Hall angle close to 90° ($\rho_{xx} \ll |\rho_{xy}|$). For example, these conditions can be met in a high-quality sample at a density close to the $\nu = 1/2$ Composite Fermion liquid state.[2]

A. Current distribution

Under the conditions stated above, Eq. (6) reduces to

$$\rho_{xx}\nabla^2\psi - \frac{\partial\psi}{\partial x}\frac{\partial\rho_{xy}}{\partial y} + \frac{\partial\psi}{\partial y}\frac{\partial\rho_{xy}}{\partial x} = 0\,. \qquad (13)$$

The constant parameters ρ_{xx} and $\nabla\rho_{xy}$ introduce two new lengthscales

$$\ell_x \equiv \rho_{xx}\left(\frac{\partial\rho_{xy}}{\partial x}\right)^{-1} \qquad (14)$$

$$\ell_y \equiv \rho_{xx}\left(\frac{\partial\rho_{xy}}{\partial y}\right)^{-1} \qquad (15)$$

which characterise the spatial variation of the resistivity tensor: $|\ell_x|$ ($|\ell_y|$) is the distance over which ρ_{xy} changes by ρ_{xx} in the x (y) direction.

There is a simple solution to Eq.(13) that is consistent with the boundary conditions that $j_y = 0$ at $y = 0, w$ on the top and bottom sides of the Hall bar. It is sufficient to set $\psi(\mathbf{r}) = \psi(y)$, such that $j_y = \frac{\partial\psi}{\partial x} = 0$ everywhere. Then Eq.(13) becomes

$$\frac{\partial^2\psi}{\partial y^2} = -\frac{1}{\rho_{xx}}\frac{\partial\rho_{xy}}{\partial x}\frac{\partial\psi}{\partial y},$$

i.e.

$$\frac{\partial j_x}{\partial y} = -\frac{1}{\rho_{xx}}\frac{\partial\rho_{xy}}{\partial x}j_x.$$

The solution is

$$j_x = \frac{I}{\ell_x}\frac{e^{-y/\ell_x}}{(1 - e^{-w/\ell_x})} \quad , \quad j_y = 0 \qquad (16)$$

where $I \equiv \int_0^w j_x\, dy$ is the total current flowing along the sample and ℓ_x is the characteristic lengthscale (14). The solution describes a current that is concentrated within a distance of order $|\ell_x|$ of one edge of the sample. Which edge this is depends on the sign of ℓ_x (*i.e.* the sign of $\frac{\partial\rho_{xy}}{\partial x}$ since ρ_{xx} is positive). For $\ell_x > 0$, the current is concentrated close to $y = 0$; for $\ell_x < 0$, the current is concentrated close to $y = w$.

From this solution, it is straightforward to determine the resistances that would be obtained in a four-terminal measurement on the Hall bar. We assume that the voltage probes are a distance L apart, so that, depending on the side of the sample on which these probes are placed, the two longitudinal resistances are

$$R_{12} = \frac{E_x(y=0)L}{I} = \frac{L}{\ell_x}\rho_{xx}\frac{1}{1 - e^{-w/\ell_x}} \qquad (17)$$

$$R_{43} = \frac{E_x(y=w)L}{I} = R_{12}(0)e^{-w/\ell_x} \qquad (18)$$

(We label the voltage probes in the same way as in Fig. 1. Note, however, that here we do not consider an inhomogeneous system in which there are two regions of quantized Hall states: the gradient in Hall resistivity is assumed to be uniform and constant over the whole bar.)

In the limit $w \ll |\ell_x|$, the current is spread uniformly over the width of the sample and we recover the results for a homogeneous system: the longitudinal resistance is the same on each side of the sample and set by the bulk resistivity ρ_{xx} and a geometrical factor

$$R_{12} = R_{43} = \rho_{xx}\frac{L}{w}\,.$$

In the limit $w \gg |\ell_x|$, the current is strongly confined to one side of the sample. Assuming that $\ell_x < 0$ so the current is close to the $y = w$ side, we find

$$\begin{aligned} R_{12} &= 0 \\ R_{43} &= L\left|\frac{\partial \rho_{xy}}{\partial x}\right| = |\Delta\rho_{xy}| \end{aligned}$$

(For $\ell_x > 0$ the current is pushed to the other side, so $R_{43} = 0$ and $R_{12} = |\Delta\rho_{xy}|$.) For $w \gg |\ell_x|$, on the side of the sample where the current is concentrated, the longitudinal resistance drop between the two voltage probes is set by the difference $|\Delta\rho_{xy}|$ of the Hall resistivities at these two points; on the other side the longitudinal potential vanishes. This result is identical to that for the case in which the contacts lie in two quantum Hall fluids, as discussed in §III. We emphasize, however, that the result described here applies to the very different situation of a *compressible* system in which ρ_{xy} varies smoothly in space.

Nevertheless, this solution provides an explicit example of a situation in which the voltage drop on one side of the sample is exponentially small. If the region between the quantized Hall phases of Fig. 1 were to consist of a region of linearly varying Hall resistivity, as described by the model studied in this section, the current would be tightly confined to one side of the sample within a lengthscale ℓ_x. The voltage drop on the other side of the sample would be exponentially small, and the arguments of § III can be applied. In this case, we see that the parameter controlling the exponential suppression is the ratio, $w/|\ell_x|$, of the width of the Hall bar w to the lengthscale $|\ell_x|$.

B. Extracting ρ_{xx}

It is interesting to note that even in the presence of an *unknown* gradient $\nabla\rho_{xy}$, the bulk resistivity ρ_{xx} can, in principle, be extracted from the two measured resistances R_{12}, R_{43} in this Hall bar geometry, using the results (17,18). (It is important that the conditions for validity of these results apply. These conditions are discussed further in §VII.) Our solution shows that the component of the gradient of the Hall resistivity perpendicular to the Hall bar, $\partial\rho_{xy}/\partial y$, is irrelevant for the long Hall bar (but see §V for finite samples). The component of the gradient for the Hall resistivity along the Hall bar can be deduced from (14,17,18) to be

$$\frac{\partial \rho_{xy}}{\partial x} = \frac{R_{12} - R_{43}}{L} \tag{19}$$

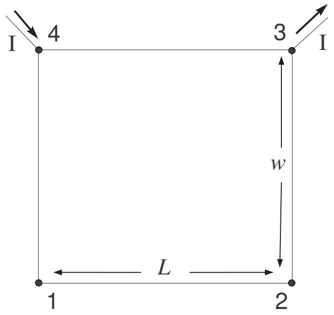

FIG. 2: Illustration of the system described in § V. Contacts are numbered $1-4$, such that contact 1 is at the origin.

Moreover, simple manipulations show that

$$\rho_{xx} = \frac{w}{L}\frac{R_{12} - R_{43}}{\ln\left[R_{12}/R_{43}\right]}. \tag{20}$$

For systems in which $|\ell_x|$ is small compared to the sample width w, the accuracy with which ρ_{xx} can be extracted becomes limited by the accuracy with which the smaller resistance can be measured. In this case, in order to extract ρ_{xx} reliably would require measurements on narrower samples, in which $w/|\ell_x|$ is of order one so that R_{12}/R_{43} is not too small or too large.

The results of this section rely on the geometry of a long Hall bar, such that in the vicinity of the voltage probes the current distribution is independent of position along the bar. We now turn to discuss the resistance that would be measured in rectangular geometries, with the current contacts at the corners.

V. TRANSPORT IN RECTANGULAR SAMPLES WITH A UNIFORM GRADIENT IN THE HALL RESISTIVITY

We now consider again a system in which there is a constant gradient to ρ_{xy}, and ρ_{xx} is independent of position. However, now we study a sample which is a rectangle of length L and width w, and in which current is injected and extracted at the corners, as described in Fig. 2. This is representative of the geometry of the samples used in Ref. 1. The important new aspect, as compared to the case of the long Hall bar, is that the current is injected into the sample in a nonuniform profile and we describe the current distribution in the whole sample, including the bending of the current flow in the vicinity of the current contacts.

We therefore aim to solve Eq. (13) again, with boundary conditions that correspond to two current contacts at the two corners $(0, w)$ and (L, w). These boundary conditions are

$$\begin{aligned} &\psi(x, y = 0) = \psi(x = 0, y) = \psi(x = L, y) = C_1 \\ &\psi(x, y = w) = C_2, \end{aligned} \tag{21}$$

where C_1, C_2 are constants. Without loss of generality, we can choose $C_1 = 0$, $C_2 = -I$. The solution to (13) with these boundary conditions is

$$\psi = \sum_{m=0}^{\infty} -I \frac{2m\pi(1-(-1)^m e^{-\frac{L}{2\ell_y}})}{(\frac{L}{2\ell_y})^2 + m^2\pi^2} \exp\left(\frac{x}{2\ell_y} - \frac{(y-w)}{2\ell_x}\right) \frac{\sinh(\frac{1}{2}\sqrt{(\frac{1}{\ell_x})^2 + 4\lambda_m}y)}{\sinh(\frac{1}{2}\sqrt{(\frac{1}{\ell_x})^2 + 4\lambda_m}w)} \sin(\frac{m\pi x}{L}), \tag{22}$$

where

$$\lambda_m = \frac{m^2\pi^2}{L^2} + \left(\frac{1}{2\ell_y}\right)^2. \tag{23}$$

We note that there are four length scales relevant to this problem: $w, L, |\ell_y|, |\ell_x|$.

In the following we examine first the case where the gradient of ρ_{xy} is in the x–direction ($\ell_y = 0$). We calculate the current profile and the longitudinal voltages on the two sides $y = 0, w$ for the cases of positive and negative ℓ_x. When $|\ell_x| \ll L, w$, we find that the current flows primarily along one of the sides, that is determined by the sign of ℓ_x. The voltages on the two sides are again different, but the presence of the contacts require a certain care in analyzing the voltage drops. Then, we examine the case of $\ell_x = 0$, where the gradient of ρ_{xy} is in the y–direction. In that case, the effect of the density gradient on the current flow is more minor.

A. Gradient in the x-direction

When $\partial\rho_{xy}/\partial y = 0$ Eq. (22) becomes

$$\psi = \sum_{m(odd)} -I\frac{4}{m\pi}\frac{\sinh(\frac{1}{2}\sqrt{4\lambda_m + \frac{1}{\ell_x^2}}y)}{\sinh(\frac{1}{2}\sqrt{4\lambda_m + \frac{1}{\ell_x^2}}w)} \times \tag{24}$$
$$\times \sin(\frac{m\pi x}{L}) \exp -\frac{(y-w)}{2\ell_x}.$$

The current components can be extracted using Eq.(5).

In the limit where $\ell_x \ll L, w$ the voltage drop along the $y = 0$ side is

$$V_{12} = \rho_{xx} \sum_{m(odd)} I \frac{8L}{m^2\pi^2 |\ell_x|} \sqrt{4m^2\pi^2\left(\frac{\ell_x}{L}\right)^2 + 1} \times$$
$$\times \exp\left(\frac{w}{2\ell_x} - \frac{1}{2}\sqrt{4m^2\pi^2\left(\frac{\ell_x}{L}\right)^2 + 1}\frac{w}{|\ell_x|}\right). \tag{25}$$

When $\ell_x < 0$, this voltage drop is exponentially small, as e^{-w/ℓ_x}. When $\ell_x > 0$, the first few terms in the sum (those with $m \ll L/|\ell_x|$) yield a significant finite contribution which is proportional to $\rho_{xx}\frac{L}{\ell_x}$, and the first correction is smaller by a factor of ℓ_x/L. Therefore we have

$$R_{12} \cong \begin{cases} 0 + \mathcal{O}(e^{-w/\ell_x}) & \ell_x < 0 \\ \rho_{xx}\frac{L}{\ell_x} = \Delta\rho_{xy} + \mathcal{O}(\rho_{xx}) & \ell_x > 0 \end{cases}. \tag{26}$$

The voltage drop on the $y = w$ edge is

$$V_{43} = -\rho_{xx} \sum_{m(odd)} I\frac{8L}{m^2\pi^2}\left(\frac{1}{2\ell_x} - \frac{1}{2}\sqrt{4\frac{m^2\pi^2}{L^2} + \frac{1}{\ell_x^2}} \times \right.$$
$$\left. \times \coth(\frac{1}{2}\sqrt{4\frac{m^2\pi^2}{L^2} + \frac{1}{\ell_x^2}}w)\right). \tag{27}$$

The second term in (27) diverges. This divergence is a result of the fact that by evaluating the voltage between $x = 0$ and $x = L$, we place our voltage probes on top of the contacts. If the probes are put at a distance ϵ from the current contacts, we obtain

$$V_{43} = -\rho_{xx} \sum_{m(odd)} I\frac{8L}{m^2\pi^2}\left(\frac{1}{2\ell_x} - \frac{1}{2}\sqrt{4\frac{m^2\pi^2}{L^2} + \frac{1}{\ell_x^2}}\right) \times$$
$$\times \cos(\frac{m\pi\epsilon}{L}) = S_2 - S_1, \tag{28}$$

where we define

$$S_1 \equiv \rho_{xx} \sum_{m(odd)} I\frac{8L}{m^2\pi^2}\frac{1}{2\ell_x}\cos(\frac{m\pi\epsilon}{L}),$$

$$S_2 \equiv \rho_{xx} \sum_{m(odd)} I\frac{8L}{m^2\pi^2}\frac{1}{2}\sqrt{4\frac{m^2\pi^2}{L^2} + \frac{1}{\ell_x^2}}\cos(\frac{m\pi\epsilon}{L}).$$

The first sum can be evaluated

$$S_1 = \rho_{xx} I(\frac{L}{2\ell_x} - \frac{|\epsilon|}{\ell_x}). \tag{29}$$

The square root in S_2 may be approximated: for $m \ll m_0$ (with $m_0 \equiv L/\pi|\ell_x|$) we have $\sqrt{4(m\pi/L)^2 + 1/\ell_x^2} \cong 1/|\ell_x|$, whereas for large values of m we have $\sqrt{4(m\pi/L)^2 + 1/\ell_x^2} \cong 2\pi m/L$. Within that approximation

$$V_{43} = \rho_{xx} I(L - 2\epsilon)\left(\frac{1}{2|\ell_x|} - \frac{1}{2\ell_x}\right) + \tag{30}$$
$$\rho_{xx} I \sum_{m(odd)=m_0}^{\infty} \frac{8L}{m^2\pi^2}\left(\frac{m\pi}{L} - \frac{1}{2|\ell_x|}\right)\cos\frac{m\pi\epsilon}{L}$$

The first term in (30) is the only term that depends on the sign of ℓ_x: when $\ell_x < 0$ it is exactly equal to $I\Delta\rho_{xy}$, where $\Delta\rho_{xy}$ is now the change in the Hall resistivity over the length $L - 2\epsilon$; when $\ell_x > 0$ Eq. (30) is hard to evaluate analytically. For $\epsilon \ll \ell_x$, the second term logarithmically diverges. This divergence, similar to that of equation (27), originates from the singular current density near a point source/sink. If $\epsilon > \ell_x$, the voltage on the $y = w$ side is much smaller than that on the $y = 0$ edge, since most of the current turns to flow on the $y = 0$ side. Its precise ϵ–dependence is hard to extract from (30).

To summarize the discussion of current flow along the ρ_{xy} gradient in a finite sample, we note that for $w \gg \ell_x$ the side along which the current flows is determined by the sign of ℓ_x and not by the position of the contacts. Along this side (which is $y = 0$ for $\ell_x > 0$ and $y = w$ for $\ell_x < 0$),as long as the the voltage contacts are sufficiently far from the current source and sink, the voltage drop is determined by the difference in ρ_{xy} between the voltage probes, and is independent of ρ_{xx}. Along the other edge the voltage drop is very small.

B. Gradient in the y-direction

In the case of a uniform gradient in the y direction, the current injected at the corners propagates primarily along the edge at $y = w$. In this case, however, the concentration of the current on the $y = w$ is a result of its injection at the corners of that side, and not a result of the density gradient. Indeed, as §.IV A shows, if the current is injected uniform in y, it stays so. As a consequence, the current profile is not exponential, and the voltage drop on the $y = w$ is not independent of ρ_{xx}. This qualitative picture comes out of Eq. (22). For $\partial\rho_{xy}/\partial x = 0$ we have

$$\psi = \sum_{m=0}^{\infty} \quad -I\frac{2m\pi(1-(-1)^m e^{-\frac{L}{2\ell_y}})}{(\frac{L}{2\ell_y})^2 + m^2\pi^2} \times \times \frac{\sinh(\sqrt{\lambda_m}y)}{\sinh(\sqrt{\lambda_m}w)} \sin(\frac{m\pi x}{L}) \exp\frac{x}{2\ell_y}. \tag{31}$$

We first consider the voltage drop along $y = 0$. As a first step we calculate $\frac{\partial\psi}{\partial y}|_{y=0}$:

$$\frac{\partial\psi}{\partial y}|_{y=0} = \sum_{m=0}^{\infty} -I\frac{2m\pi(1-(-1)^m e^{-\frac{L}{2\ell_y}})}{(\frac{L}{2\ell_y})^2 + m^2\pi^2} \times \times \sin(\frac{m\pi x}{L}) \exp\frac{x}{2\ell_y} \frac{\sqrt{\lambda_m}}{\sinh(\sqrt{\lambda_m}w)}. \tag{32}$$

Taking the limit of $\ell_y \ll L, w$ we can write $\sinh(\sqrt{\lambda_m}w) = 1/2\exp(\sqrt{\lambda_m}w)$. An overestimate of the sum may be obtained by replacing $\sqrt{\lambda_m}\exp(-\sqrt{\lambda_m}w)$ by $\sqrt{\lambda_0}\exp(-\sqrt{\lambda_0}w)$. Since for $0 < x < L$

$$\sum_{m=0}^{\infty} \frac{2m\pi(1-(-1)^m e^{-\frac{L}{2\ell_y}})}{(\frac{L}{2\ell_y})^2 + m^2\pi^2} \sin\frac{m\pi x}{L} = \exp -\frac{x}{2\ell_y}, \tag{33}$$

we get that

$$\left.\frac{\partial\psi}{\partial y}\right|_{y=0} = -I\sqrt{\lambda_0}\exp(-\sqrt{\lambda_0}w) = -I/2\,|\ell_y|\exp(-w/2\,|\ell_y|), \tag{34}$$

leading, when integrated over x, to an exponentially small voltage drop regardless of the sign of the gradient of ρ_{xy}.

At $y = w$, we can expect to have the same voltage drop for both positive and negative gradients. We note that the expression for the current in the x direction remains unchanged when replacing ℓ_y with $-\ell_y$, along with replacing x by $L - x$; therefore, it is enough to consider only the case when ℓ_y is positive. Integrating j_x with respect to x and taking the limit of $\ell_y \ll L, w$ we find the potential difference between the points x_4 and x_3 to be

$$V_{43} = -\rho_{xx}\int_{x_3}^{x_4} j_x dx \cong \sum_{m=0}^{\infty} \rho_{xx} I \frac{2m\pi L(1-(-1)^m e^{-\frac{L}{2\ell_y}})}{\left(\sqrt{(\frac{L}{2\ell_y})^2 + m^2\pi^2}\right)^3} \left(\frac{1}{2\ell_y}\sin(\frac{m\pi x}{L}) - \frac{m\pi}{L}\cos(\frac{m\pi x}{L})\right) \exp\frac{x}{2\ell_y}\Big|_{x_4}^{x_3}. \tag{35}$$

We calculate the voltage between $x_4 = \epsilon$ and $x_3 = L - \epsilon$, in the limit of $\epsilon \gg \ell_y$. Replacing summation by integration, we obtain

$$V_{43} \cong \rho_{xx} I \frac{2}{\pi}\left(\frac{x}{2\ell_y}K_0\left(\frac{x}{2\ell_y}\right) + \frac{x}{2\ell_y}K_1\left(\frac{x}{2\ell_y}\right) - K_0\left(\frac{x}{2\ell_y}\right)\right) \exp\frac{x}{2\ell_y}\Big|_{\epsilon}^{L-\epsilon}. \tag{36}$$

The leading terms are

$$V_{43} \sim \sqrt{\rho_{xx} \Delta \rho_{xy}^{L-\epsilon}}I - \sqrt{\rho_{xx} \Delta \rho_{xy}^{\epsilon}}I \tag{37}$$

where

$$\Delta \rho_{xy}^{L-\epsilon} = \frac{\partial \rho_{xy}}{\partial y}(L-\epsilon),$$
$$\Delta \rho_{xy}^{\epsilon} = \frac{\partial \rho_{xy}}{\partial y}\epsilon.$$

This time, the voltage explicitly depends on ρ_{xx}, as the width of the strip within which the current flows does not scale as ρ_{xx}^{-1}.

VI. UNIFORM DISSIPATIVE REGION BETWEEN TWO QUANTUM HALL REGIONS

We now consider in detail a situation in which there are quantized Hall states at the two ends of the sample as in Fig. 1, with Hall resistivities ρ_{xy}^A and ρ_{xy}^B and vanishing longitudinal resistivity. In between there must be a dissipative region, where the local dissipative resistivity ρ_{xx} is not necessarily small compared to ρ_{xy}. In general, the resistivity in this region will be x–dependent. However, we simplify and consider the central region as having longitudinal resistivity ρ_{xx}^C and Hall resistivity ρ_{xy}^C that do not vary in position (see Fig. 3).

Since the resistivity components vary along the x direction only, Eq. (6) becomes

$$\rho_{xx}(x)\nabla^2\psi + \rho'_{xy}(x)\frac{\partial \psi}{\partial y} + \rho'_{xx}(x)\frac{\partial \psi}{\partial x} = 0 \tag{38}$$

where $\rho'_{ij} \equiv \frac{\partial \rho_{ij}}{\partial x}$. Thus, in the central region where $\rho'_{ij} = 0$, the stream function ψ simply obeys the Laplace equation. The interfaces to the quantized Hall regions A and B impose boundary conditions on the current density (and hence on ψ). Conservation of the electric field parallel to the interface and of the current density perpendicular to the interface, leads to

$$\frac{j_x}{j_y} = \begin{cases} -\frac{\rho_{xx}^C}{\rho_{xy}^A - \rho_{xy}^C} & x = 0, \\ \\ -\frac{\rho_{xx}^C}{\rho_{xy}^B - \rho_{xy}^C} & x = L, \end{cases} \tag{39}$$

where $j_x = -\partial\psi/\partial y$, $j_y = \partial\psi/\partial x$ are the components of the current density inside the central dissipative region. At the $y = 0$ and $y = w$ edges of the sample the current must be parallel to the edge, *i.e.*

$$j_y(y=0) = j_y(y=w) = 0. \tag{40}$$

We simplify matters by using a conformal mapping[12]. We introduce a complex potential

$$V = \chi + \imath\psi \tag{41}$$

where ψ is the stream function. The function V is analytic in $z = x + \imath y$ and hence ψ obeys the Laplace equation. Using the Cauchy-Reimann equations we may find the full derivative of V with respect to z

$$\frac{dV}{dz} = -j_x + \imath j_y. \tag{42}$$

So the full derivative of the complex potential is a linear combination of the components of the current density. If we define

$$\frac{dV}{dz} = e^{f(z)} \tag{43}$$

where $f(z)$ is an analytic function, we get that

$$j_x = -e^{\mathrm{Re}(f(z))}\cos \mathrm{Im}(f(z)), \tag{44}$$
$$j_y = e^{\mathrm{Re}(f(z))}\sin \mathrm{Im}(f(z)). \tag{45}$$

The boundary conditions set for the stream function ψ can now be translated into conditions on the function $f(z)$. The requirement on setting j_y to zero at $y = (0, w)$ is translated into setting the imaginary part of $f(z)$ to zero there. The boundary conditions at $x = (0, L)$ can be translated into

$$\tan \mathrm{Im} f(z) = \begin{cases} \frac{\rho_{xy}^A - \rho_{xy}^C}{\rho_{xx}^C} & x = 0, \\ \\ \frac{\rho_{xy}^B - \rho_{xy}^C}{\rho_{xx}^C} & x = L. \end{cases} \tag{46}$$

Once we have solved for the imaginary part of $f(z)$, $f(z)$ is completely determined, and therefore the electric field and current distribution are known up to a normalization factor, which determines the current direction and magnitude. We find

$$f(z) = \sum_{n(odd)=1}^{\infty} \frac{4}{n\pi}\left(\sinh\frac{n\pi L}{2w}\right)^{-1} \times \tag{47}$$
$$\times \left(\beta_B \cosh\frac{n\pi z}{w} - \beta_A \cosh\frac{n\pi(z-L)}{w}\right)$$

where $\beta_A \equiv \arctan[(\rho_{xy}^A - \rho_{xy}^C)/\rho_{xx}^C]$, $\beta_B \equiv \arctan[(\rho_{xy}^B - \rho_{xy}^C)/\rho_{xx}^C]$. Since the intermediate region is a transition region between the two quantized Hall states on its ends, ρ_{xy}^C is intermediate between ρ_{xy}^A and ρ_{xy}^B. Thus, one of the numbers β_A and β_B is negative and the other is positive. We set $\beta_A < 0$ and $\beta_B > 0$. Evaluating $f(z)$ on the boundary at $x = L$ we get:

$$\mathrm{Im} f(x=L, y) = \sum_{n(odd)=1}^{\infty} \frac{4\beta_B}{n\pi}\sin\frac{n\pi y}{w} = \beta_B,$$
$$\mathrm{Re} f(x=L, y) = \sum_{n(odd)=1}^{\infty} \frac{4}{n\pi}\cos\frac{n\pi y}{w} \times$$
$$\times \left(\beta_B \coth\frac{n\pi L}{w} - \frac{\beta_A}{\sinh\frac{n\pi L}{w}}\right). \tag{48}$$

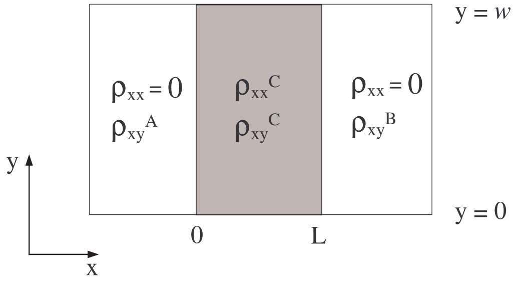

FIG. 3: The three different regions of the system described in § VI.

At the corners $y = (0, w)$ the real part of $f(z)$ diverges, going to $+\infty$ at $y = 0$, and $-\infty$ at $y = w$. This divergence implies the current density diverges at the corner $(L, 0)$ of the dissipative region, and vanishes at (L, w). The same behaviour is observed at $x = 0$, implying that current enters and leaves the dissipative region from the corners. Interchanging the signs of β_A and β_B moves the points of divergence to the line $y = w$.

In the limit where $w \gg L$, for every x in the range $0 < x < L$ we get

$$\mathrm{Re} f(x, y) \simeq \sum_{n(odd)=1}^{\infty} \frac{4(\beta_B - \beta_A)w}{\pi^2 L} \frac{\cos\frac{n\pi y}{w}}{n^2}. \tag{49}$$

This sum can be carried out explicitly to obtain

$$\mathrm{Re} f(x, y) \simeq \frac{(\beta_B - \beta_A)}{L} \left(\frac{w}{2} - |y|\right). \tag{50}$$

implying the current density to be large near the edge at $y = 0$, and decay exponentially as a function of y. The decay length is $\ell = L/(\beta_B - \beta_A)$. In the limit of small dissipation where $\rho_{xx}^{C} \ll |\rho_{xy}^{A,B} - \rho_{xy}^{C}|$ we have $|\beta_{A,B}| \to \pi/2$ and the decay length approaches the limit $\ell = L/\pi$. In the opposite limit of large dissipation where $\rho_{xx}^{C} \gg |\rho_{xy}^{A,B} - \rho_{xy}^{C}|$, the decay length grows like $\rho_{xx}^{C}/|\rho_{xy}^{A} - \rho_{xy}^{B}|$. As long as this length is smaller than w, the current is still concentrated along one side of the sample, and the longitudinal voltage on that side is determined by $\rho_{xy}^{A} - \rho_{xy}^{B}$, rather than by ρ_{xx}. Again, interchanging the sign of β_A and β_B switches the edge where the current propagates from $y = 0$ to $y = w$.

VII. DISCUSSION

In this work we discussed the effect of density inhomogeneities on the measurement of the longitudinal resistance in quantum Hall systems.

We analyzed the case in which the two ends of the sample are in two different quantized Hall states, separated by a dissipative transition region. Generically, in this situation we find the current flow to be concentrated along one of the edges. We showed that when that happens, the voltage along that edge is controlled by the difference in Hall resistivities between the voltage probes, while the voltage on the other edge is very small. These observations, which are largely independent of the specific spatial dependence of both ρ_{xx} and ρ_{xy} in the dissipative region, correspond to what is observed in the experiment. We solved in detail two simplified models, which indeed showed a concentration of the current along one of the edges.

In one of the models we solved, the longitudinal resistivity is assumed independent of position, and the Hall resistivity has a uniform gradient. In such a case, the current behavior is controlled by the two length scales ℓ_x and ℓ_y. For samples large compared to these length scales, the current flows in a very asymmetric way through the sample. This has been illustrated by explicit calculations in rectangular geometries, both for the ideal case of a long system, and for a rectangular system where the location of the contacts has to be taken into account. We have shown that in both cases, when the gradient is in the direction along which the current flows, the longitudinal resistance will be $\Delta\rho_{xy}$ on one side of the sample, and much smaller on the other. For the long system, we have shown that this result still holds, even if in addition there is a transverse component to the gradient.

For a long Hall bar geometry with a linear gradient in the local Hall resistivity, we showed how the microscopic resistivity ρ_{xx} can be extracted from the measurements of the longitudinal voltage drop on the two sides of the sample, via Eq. (20). We believe that this model can be of application to the cases of transport measurements on compressible states in the quantum Hall regime, for example the $\nu = 1/2$ composite-fermion liquid state in high quality samples. The conditions for application of this model to experiment relies on the validity of the assumptions used to derive Eq. (13). Firstly, these assumptions require that the variation in ρ_{xx} over the size of the sample is small compared to its average value; typically this means that the fractional change in carrier density should be small. (We note, however, that for a system with small dissipation, $\rho_{xx} \ll |\rho_{xy}|$ – that is with a local Hall angle close to 90° – even a small fractional change in carrier density can allow the change in the Hall resistivity ρ_{xy} to be large compared to ρ_{xx}.) Secondly, we have assumed that we can retain only the linear gradient in the local Hall resistivity $\rho_{xy}(\mathbf{r})$. The validity of this assumption depends on the functional form of $\rho_{xy}(\mathbf{r})$. In the case where variations in $\rho_{xy}(\mathbf{r})$ are all on the same characteristic length scale, which we shall refer to as the macroscopic correlation length ξ_M, this assumption is valid provided $\xi_M \gg L, \min(w, \ell_x)$. In practice, ξ_M can be very large, set by inhomogeneities in the growth of the samples related to characteristics of MBE machines. In realistic high mobility 2DEGs, one anticipates that there are additional inhomogeneities on a microscopic length-scale, ξ_m, of order the spacer-layer thickness. The model remains valid provided this additional lengthscale is sufficiently small, $\xi_m \ll L, \min(w, \ell_x)$, that these microscopic inhomogeneities simply affect the effective local resistivity tensor which varies smoothly on the longer lengthscale ξ_M.

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APPENDIX: CALCULATION OF THE DISSIPATED POWER

Using the same approach as in Ref. 7, we derive expressions for the power dissipation in a sample with quantized Hall states A and B at the two ends, as in Fig. 1. The central region has arbitrary local resistivity tensor.

The power dissipation is given by

$$Q = \int\int \mathbf{E}(\mathbf{r}) \cdot \mathbf{j}(\mathbf{r})\, d^2\mathbf{r}.$$

Since in regions A and B the resistivity tensor has only off-diagonal elements which are non zero, in these two regions equations (5) (4) and (1) can be combined into a single equation,

$$\rho \nabla \psi = -\nabla \phi, \tag{A.1}$$

where ρ is a scalar, equal to ρ^A_{xy}, ρ^B_{xy} in regions A and B. This equation can now be integrated to obtain the relation between ϕ and ψ:

$$\phi = -\rho\psi + c, \tag{A.2}$$

where c is a constant, in principle different for regions A and B. Writing Q in terms of these scalar functions and using Stokes' theorem, the dissipation integral becomes

$$Q = -\int (\psi \nabla \phi) \cdot d\mathbf{l}. \tag{A.3}$$

We now integrate over a rectangle that encloses the central region, as demonstrated in Fig. 1. We note that at $y = (0, w)$, the stream function ψ must be a constant, since we do not allow current to flow in the y direction. We denote $\psi(y = 0) \equiv \psi_b$ and $\psi(y = w) \equiv \psi_t$, with

$$I = \psi_b - \psi_t \tag{A.4}$$

being the total current flowing from left to right. Performing the integration we get

$$\begin{aligned} Q = -\psi_b(\phi_2 - \phi_1) - \psi_t(\phi_4 - \phi_3) + \\ \frac{1}{2}(\psi_b^2 - \psi_t^2)(\rho^A_{xy} - \rho^B_{xy}). \end{aligned} \tag{A.5}$$

Using (A.2,A.4) we can write

$$\begin{aligned} Q &= \frac{1}{2} I^2 (\rho^A_{xy} - \rho^B_{xy}) + I(\phi_1 - \phi_2) & \text{(A.6)} \\ &= \frac{1}{2} I^2 (\rho^B_{xy} - \rho^A_{xy}) + I(\phi_4 - \phi_3). & \text{(A.7)} \end{aligned}$$

Note that in §III we argue that the potential drop along one side of the sample can become exponentially small. Clearly, from (A.6) if $V_{12} = \phi_1 - \phi_2$ is to be vanishingly small, then we must have $\rho^A_{xy} - \rho^B_{xy} > 0$ such that the power loss is positive; similarly from (A.7) $V_{43} = \phi_4 - \phi_3$ can be vanishingly small only if $\rho^A_{xy} - \rho^B_{xy} < 0$.

The general result can be stated most clearly by noting that, using (A.2,A.4), we can express the current in terms of voltages as

$$I = \frac{V_{41} - V_{32}}{\rho^A_{xy} - \rho^B_{xy}} = \frac{V_{43} - V_{12}}{\rho^A_{xy} - \rho^B_{xy}}. \tag{A.8}$$

Substituting this in (A.6) one then obtains

$$Q = \frac{1}{2}(\rho^A_{xy} - \rho^B_{xy})^{-1}(V_{43}^2 - V_{12}^2), \tag{A.9}$$

which indicates that $|V_{43}| > |V_{12}|$ for $\rho^A_{xy} > \rho^B_{xy}$, and vice versa, as discussed in §III.

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[13] Strictly speaking **E** is (minus) the gradient of the electrochemical potential, and **j** is the transport current density.